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## FSB50450UD Motion SPM<sup>®</sup> 5 Series

## Features

- UL Certified No. E209204 (UL1557)
- 500 V R<sub>DS(on)</sub> = 2.4 Ω(Max) FRFET MOSFET 3-Phase Inverter with Gate Drivers and Protection
- Built-In Bootstrap Diodes Simplify PCB Layout
- Separate Open-Source Pins from Low-Side MOSFETs for Three-Phase Current-Sensing
- Active-HIGH Interface, Works with 3.3 / 5 V Logic, Schmitt-trigger Input
- Optimized for Low Electromagnetic Interference
- HVIC for Gate Driving and Under-Voltage Protection
- Isolation Rating: 1500 V<sub>rms</sub> / min.
- RoHS Compliant

## Applications

 3-Phase Inverter Driver for Small Power AC Motor Drives

## **Related Source**

 <u>AN-9082 - Motion SPM5 Series Thermal Performance</u> <u>by Contact Pressure</u>

## **General Description**

The FSB50450UD is an advanced Motion SPM<sup>®</sup> 5 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC and PMSM motors. These modules integrate optimized gate drive of the built-in MOSFETs (FRFET® technology) to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockouts and thermal monitoring. The built-in high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's internal MOSFETs. Separate open-source MOSFET terminals are available for each phase to support the widest variety of control algorithms.



## Package Marking & Ordering Information

Device	Device Marking	Package	Packing Type	Quantity
FSB50450UD	FSB50450UD	SPM5R-023	Rail	15

January 2014

## **Absolute Maximum Ratings**

**Inverter Part** (each MOSFET unless otherwise specified.)

Symbol	Parameter	Parameter Conditions		Unit
V <sub>DSS</sub>	Drain-Source Voltage of Each MOSFET		500	V
*I <sub>D 25</sub>	Each MOSFET Drain Current, Continuous	$T_{C} = 25^{\circ}C$	1.5	A
*I <sub>D 80</sub>	Each MOSFET Drain Current, Continuous	$T_{C} = 80^{\circ}C$	1.1	А
*I <sub>DP</sub>	Each MOSFET Drain Current, Peak	T <sub>C</sub> = 25°C, PW < 100 μs	3.8	А
*P <sub>D</sub>	Maximum Power Dissipation	$T_{C} = 25^{\circ}C$ , For Each MOSFET	14	W

Control Part (each HVIC unless otherwise specified.)

Symbol	Parameter	Conditions	Rating	Unit
V <sub>CC</sub>	Control Supply Voltage	Applied Between $V_{CC}$ and COM	20	V
V <sub>BS</sub>	High-side Bias Voltage	Applied Between $V_B$ and $V_S$	20	V
V <sub>IN</sub>	Input Signal Voltage	Applied Between IN and COM	$-0.3 \sim V_{CC} + 0.3$	V

Bootstrap Diode Part (each bootstrap diode unless otherwise specified.)

Symbol	Parameter	Parameter Conditions		Unit
V <sub>RRMB</sub>	Maximum Repetitive Reverse Voltage		500	V
* I <sub>FB</sub>	Forward Current	$T_{C} = 25^{\circ}C$	0.5	A
* I <sub>FPB</sub>	Forward Current (Peak)	T <sub>C</sub> = 25°C, Under 1ms Pulse Width	2.0	А

#### **Thermal Resistance**

Symbol	Parameter	Conditions	Rating	Unit
$R_{ ext{ heta}JC}$	Junction to Case Thermal Resistance	Each MOSFET under Inverter Oper- ating Condition (1st Note 1)	8.9	°C/W

### **Total System**

Symbol	Parameter	Conditions	Rating	Unit
TJ	Operating Junction Temperature		-40 ~ 150	°C
T <sub>STG</sub>	Storage Temperature		-40 ~ 125	°C
V <sub>ISO</sub>	Isolation Voltage	60 Hz, Sinusoidal, 1 Minute, Con- nect Pins to Heat Sink Plate	1500	V <sub>rms</sub>

1st Notes:

1. For the measurement point of case temperature  $T_{\mbox{C}},$  please refer to Figure 4.

2. Marking "  $^{\star}$  " is calculation value or design factor.

2

Pin descriptions				
Pin Number	Pin Name	Pin Description		
1	СОМ	IC Common Supply Ground		
2	V <sub>B(U)</sub>	Bias Voltage for U Phase High Side MOSFET Driving		
3	V <sub>CC(U)</sub>	Bias Voltage for U Phase IC and Low Side MOSFET Driving		
4	IN <sub>(UH)</sub>	Signal Input for U Phase High-Side		
5	IN <sub>(UL)</sub>	Signal Input for U Phase Low-Side		
6	V <sub>S(U)</sub>	Bias Voltage Ground for U Phase High Side MOSFET Driving		
7	V <sub>B(V)</sub>	Bias Voltage for V Phase High Side MOSFET Driving		
8	V <sub>CC(V)</sub>	Bias Voltage for V Phase IC and Low Side MOSFET Driving		
9	IN <sub>(VH)</sub>	Signal Input for V Phase High-Side		
10	IN <sub>(VL)</sub>	Signal Input for V Phase Low-Side		
11	V <sub>S(V)</sub>	Bias Voltage Ground for V Phase High Side MOSFET Driving		
12	V <sub>B(W)</sub>	Bias Voltage for W Phase High Side MOSFET Driving		
13	V <sub>CC(W)</sub>	Bias Voltage for W Phase IC and Low Side MOSFET Driving		
14	IN <sub>(WH)</sub>	Signal Input for W Phase High-Side		
15	IN <sub>(WL)</sub>	Signal Input for W Phase Low-Side		
16	V <sub>S(W)</sub>	Bias Voltage Ground for W Phase High Side MOSFET Driving		
17	Р	Positive DC-Link Input		
18	U	Output for U Phase		
19	NU	Negative DC-Link Input for U Phase		
20	N <sub>V</sub>	Negative DC–Link Input for V Phase		
21	V	Output for V Phase		
22	N <sub>W</sub>	Negative DC–Link Input for W Phase		
23	W	Output for W Phase		



### Figure 1. Pin Configuration and Internal Block Diagram (Bottom View)

1st Notes:

3. Source terminal of each low-side MOSFET is not connected to supply ground or bias voltage ground inside Motion SPM<sup>®</sup> 5 product. External connections should be made as indicated in Figure 3.

FSB50450UD Motion SPM® 5 Series

### Electrical Characteristics (T<sub>J</sub> = 25°C, V<sub>CC</sub> = V<sub>BS</sub> = 15 V unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV <sub>DSS</sub>	Drain - Source Breakdown Voltage	V <sub>IN</sub> = 0 V, I <sub>D</sub> = 250 μA (2nd Note 1)	500	-	-	V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Tem- perature Coefficient	$I_D = 250 \mu A$ , Referenced to 25°C	-	0.53	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>IN</sub> = 0 V, V <sub>DS</sub> = 500 V	-	-	250	μA
R <sub>DS(on)</sub>	Static Drain - Source Turn-On Resistance	V <sub>CC</sub> = V <sub>BS</sub> = 15 V, V <sub>IN</sub> = 5 V, I <sub>D</sub> = 0.5 A	-	1.9	2.4	Ω
V <sub>SD</sub>	Drain - Source Diode Forward Voltage	$V_{CC} = V_{BS} = 15V, V_{IN} = 0 V, I_{D} = -0.5 A$	-	-	1.2	V
t <sub>ON</sub>			-	1250	-	ns
t <sub>OFF</sub>		$V_{PN} = 300 \text{ V}, V_{CC} = V_{BS} = 15 \text{ V}, I_D = 0.5 \text{ A}$	-	500	-	ns
t <sub>rr</sub>	Switching Times	V <sub>IN</sub> = 0 V ↔ 5 V, Inductive Load L = 3 mH High- and Low-Side MOSEET Switching	-	200	-	ns
E <sub>ON</sub>		(2nd Note 2)	-	80	-	μJ
E <sub>OFF</sub>			-	10	-	μJ
RBSOA	Reverse Bias Safe Oper- ating Area	$      V_{PN} = 400 \text{ V},  \text{V}_{CC} = \text{V}_{BS} = 15 \text{ V},  \text{I}_{D} = \text{I}_{DP},  \text{V}_{DS} = \text{BV}_{DSS}, $ $\text{T}_{J} = 150^{\circ}\text{C} $ High- and Low-Side MOSFET Switching (2nd Note 3)		Full	Square	

**Inverter Part** (each MOSFET unless otherwise specified.)

#### Control Part (each HVIC unless otherwise specified.)

Symbol	Parameter		Conditions	Min	Тур	Max	Unit
I <sub>QCC</sub>	Quiescent V <sub>CC</sub> Current	V <sub>CC</sub> = 15 V, V <sub>IN</sub> = 0 V	Applied Between $V_{CC}$ and COM	-	-	160	μΑ
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> Current	V <sub>BS</sub> = 15 V, V <sub>IN</sub> = 0 V	Applied Between V <sub>B(U)</sub> - U, V <sub>B(V)</sub> - V, V <sub>B(W)</sub> - W	-	-	100	μΑ
UV <sub>CCD</sub>	Low-Side Under-Voltage	V <sub>CC</sub> Under-Voltage	Protection Detection Level	7.4	8.0	9.4	V
UV <sub>CCR</sub>	Protection (Figure 8)	V <sub>CC</sub> Under-Voltage	Protection Reset Level	8.0	8.9	9.8	V
UV <sub>BSD</sub>	High-Side Under-Voltage	V <sub>BS</sub> Under-Voltage	Protection Detection Level	7.4	8.0	9.4	V
UV <sub>BSR</sub>	Protection (Figure 9)	V <sub>BS</sub> Under-Voltage	Protection Reset Level	8.0	8.9	9.8	V
V <sub>IH</sub>	ON Threshold Voltage	Logic High Level	Applied between IN and COM	2.9	-	-	V
V <sub>IL</sub>	OFF Threshold Voltage	Logic Low Level	Applied between in and COM	-	-	0.8	V
I <sub>IH</sub>	Input Rise Current	$V_{IN} = 5V$	Applied between IN and COM	-	10	20	μA
۱ <sub>IL</sub>	Input bias Cuffent	$V_{IN} = 0V$	Applied between IN and COM	-	-	2	μA

Bootstrap Diode Part (each bootstrap diode unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{FB}$	Forward Voltage	$I_F = 0.1 \text{ A}, T_C = 25^{\circ}\text{C} \text{ (2nd Note 5)}$	-	2.0	-	V
t <sub>rrB</sub>	Reverse Recovery Time	I <sub>F</sub> = 0.1 A, T <sub>C</sub> = 25°C	-	80	-	ns

2nd Notes:

4. Built-in bootstrap diode includes around  $15 \Omega$  resistance characteristic. Please refer to Figure 2.

<sup>1.</sup> BV<sub>DSS</sub> is the absolute maximum voltage rating between drain and source terminal of each MOSFET inside Motion SPM<sup>®</sup> 5 product. V<sub>PN</sub> should be sufficiently less than this value considering the effect of the stray inductance so that V<sub>PN</sub> should not exceed BV<sub>DSS</sub> in any case.

<sup>2.</sup> t<sub>ON</sub> and t<sub>OFF</sub> include the propagation delay of the internal drive IC. Listed values are measured at the laboratory test condition, and they can be different according to the field applications due to the effect of different printed circuit boards and wirings. Please see Figure 5 for the switching time definition with the switching test circuit of Figure 6.

<sup>3.</sup> The peak current and voltage of each MOSFET during the switching operation should be included in the Safe Operating Area (SOA). Please see Figure 6 for the RBSOA test circuit that is same as the switching test circuit.

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## **Recommended Operating Condition**

0.3 0.2 0.1 0.0

0 1

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V <sub>PN</sub>	Supply Voltage	Applied Between P and N	-	300	400	V
V <sub>CC</sub>	Control Supply Voltage	Applied Between $V_{CC}$ and COM	13.5	15.0	16.5	V
V <sub>BS</sub>	High-Side Bias Voltage	Applied Between $V_B$ and $V_S$	13.5	15.0	16.5	V
V <sub>IN(ON)</sub>	Input ON Threshold Voltage	Applied Between IN and COM	3.0	-	V <sub>CC</sub>	V
V <sub>IN(OFF)</sub>	Input OFF Threshold Voltage	Applied Between IN and COM	0	-	0.6	V
t <sub>dead</sub>	Blanking Time for Preventing Arm-Short	$V_{CC}$ = $V_{BS}$ = 13.5 ~ 16.5 V, $T_{J}\ \leq 150^{\circ}C$	1.0	-	-	μS
f <sub>PWM</sub>	PWM Switching Frequency	$T_{J} \leq 150^{\circ}C$	-	15	-	kHz



Figure 2. Built-in Bootstrap Diode Characteristics (Typical)

 $V_{F}[V]$ 

8

9 10

11 12 13

14 15

Tc=25°C

5

6 7

2 3 4



#### Figure 3. Recommended MCU Interface and Bootstrap Circuit with Parameters

#### 3rd Notes:

- 1. Parameters for bootstrap circuit elements are dependent on PWM algorithm. For 15 kHz of switching frequency, typical example of parameters is shown above.
- 2. RC-coupling (R<sub>5</sub> and C<sub>5</sub>) and C<sub>4</sub> at each input of Motion SPM 5 product and MCU (Indicated as Dotted Lines) may be used to prevent improper signal due to surge-noise.
- Bold lines should be short and thick in PCB pattern to have small stray inductance of circuit, which results in the reduction of surge-voltage. Bypass capacitors such as C<sub>1</sub>, C<sub>2</sub> and C<sub>3</sub> should have good high-frequency characteristics to absorb high-frequency ripple-current.



#### Figure 4. Case Temperature Measurement

#### 3rd Notes:

4. Attach the thermocouple on top of the heat-sink of SPM 5 package (between SPM 5 package and heatsink if applied) to get the correct temperature measurement.





### Figure 9. Example of Application Circuit

1. About pin position, refer to Figure 1.

4th Notes:

2. RC-coupling (R<sub>5</sub> and C<sub>5</sub>, R<sub>4</sub> and C<sub>6</sub>) and C<sub>4</sub> at each input of Motion SPM<sup>®</sup> 5 product and MCU are useful to prevent improper input signal caused by surge-noise.

3. The voltage-drop across R<sub>3</sub> affects the low-side switching performance and the bootstrap characteristics since it is placed between COM and the source terminal of the lowside MOSFET. For this reason, the voltage-drop across R<sub>3</sub> should be less than 1 V in the steady-state.

4. Ground-wires and output terminals, should be thick and short in order to avoid surge-voltage and malfunction of HVIC.

5. All the filter capacitors should be connected close to Motion SPM 5 product, and they should have good characteristics for rejecting high-frequency ripple current.



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http://www.fairchildsemi.com/dwg/MO/MOD23DB.pdf

FSB50450UD Motion SPM® 5 Series



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